BAS16H, SBAS16H

Switching Diode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	V _R	75	Vdc
Peak Forward Current	١ _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$ Derate above 25°C	PD	200 1.57	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	°C/W
Junction and Storage Temperature	T _J , T _{stg}	–55 to 150	°C

1. FR-4 Minimum Pad.



ON Semiconductor®

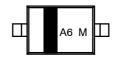
http://onsemi.com





CASE 477 STYLE 1

MARKING DIAGRAM



A6 = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
BAS16HT1G	SOD-323 (Pb-Free)	3000 / Tape & Reel
SBAS16HT1G	SOD-323 (Pb-Free)	3000 /T ape & Reel
SBAS16HT3G	SOD-323 (Pb-Free)	10000 / Tape & Reel

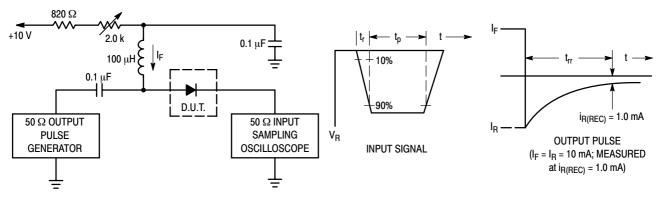
+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

BAS16H, SBAS16H

ELECTRICAL CHARACTERISTICS (T_A = 25° C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS			-	
Reverse Voltage Leakage Current $(V_R = 75 \text{ Vdc})$ $(V_R = 75 \text{ Vdc}, T_J = 150^{\circ}\text{C})$ $(V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C})$	IR	- - -	1.0 50 30	μAdc
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	75	-	Vdc
Forward Voltage $(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V _F	- - -	715 855 1000 1250	mV
Diode Capacitance (V _R = 0, f = 1.0 MHz)	CD	_	2.0	pF
Forward Recovery Voltage (I _F = 10 mAdc, t _r = 20 ns)	V _{FR}	-	1.75	Vdc
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, R_L = 50 \Omega)$	t _{rr}	-	6.0	ns
Stored Charge (I _F = 10 mAdc to V _R = 5.0 Vdc, $R_L = 500 \Omega$)	Q _S	-	45	рС

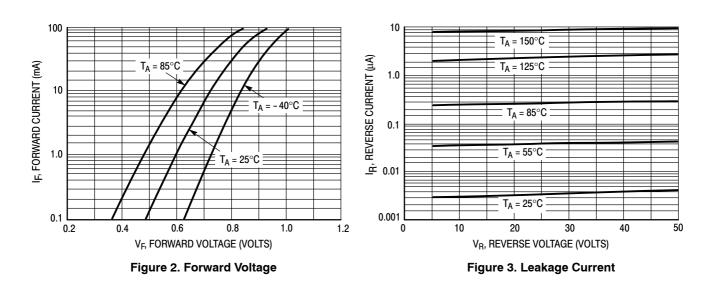
BAS16H, SBAS16H

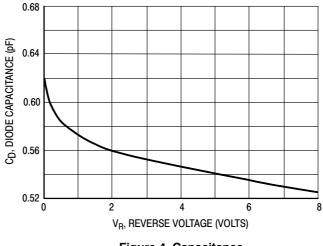


Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA. 2. Input pulse is adjusted so I_{R(peak)} is equal to 10 mA.



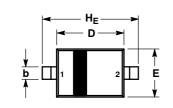
Figure 1. Recovery Time Equivalent Test Circuit

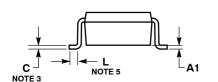




PACKAGE DIMENSIONS

SOD-323 CASE 477-02 ISSUE H







NOTES:

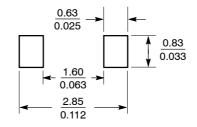
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS.
 LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
- 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 5. DIMENSION L IS MEASURED FROM END OF RADIUS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0	.006 RE	F
b	0.25	0.32	0.4	0.010	0.012	0.016
С	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

STYLE 1:

PIN 1. CATHODE (POLARITY BAND) 2. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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